

ABSTRACT

When a SOI substrate is produced a first silicon layer epitaxially grown on the insulating underlay is ion implanted to make deep part of interface of the silicon layer amorphous, and then annealed to recrystallize. Next, the silicon layer is heat treated to oxidize part of the surface side, and after the silicon oxide is removed by etching, a silicon layer is epitaxially grown on the remaining first silicon layer to form a second silicon layer. Subsequently, the second silicon layer is again ion implanted to make deep part of interface amorphous, then annealing is performed to recrystallize. With this method, a SOI substrate, which is very small in crystal defect density of the silicon layer and good in surface flatness, can be produced. Therefore, on the semiconductor substrate an electronic device or optical device having high device performance and reliability can be realized.